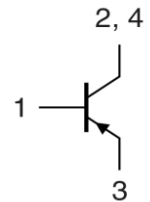
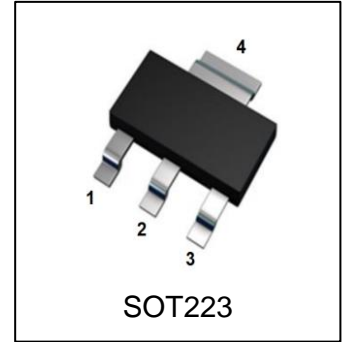


# LBSS5350SZ4TZHG

## S-LBSS5350SZ4TZHG

### PNP TRANSISTOR



#### 1. FEATURES

- Low collector-to-emitter saturation voltage.
- Fast switching speed.
- Large current capacity and wide ASO.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

#### 2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS5350SZ4TZHG	A6	1000/Tape&Reel

#### 3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-50	V
Collector–Base Voltage	VCBO	-60	V
Emitter–Base Voltage	VEBO	-6	V
Collector Current	IC	-3	A
Collector Current(Pulse)	ICP	-6	A
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

#### 4. THERMAL CHARACTERISTICS

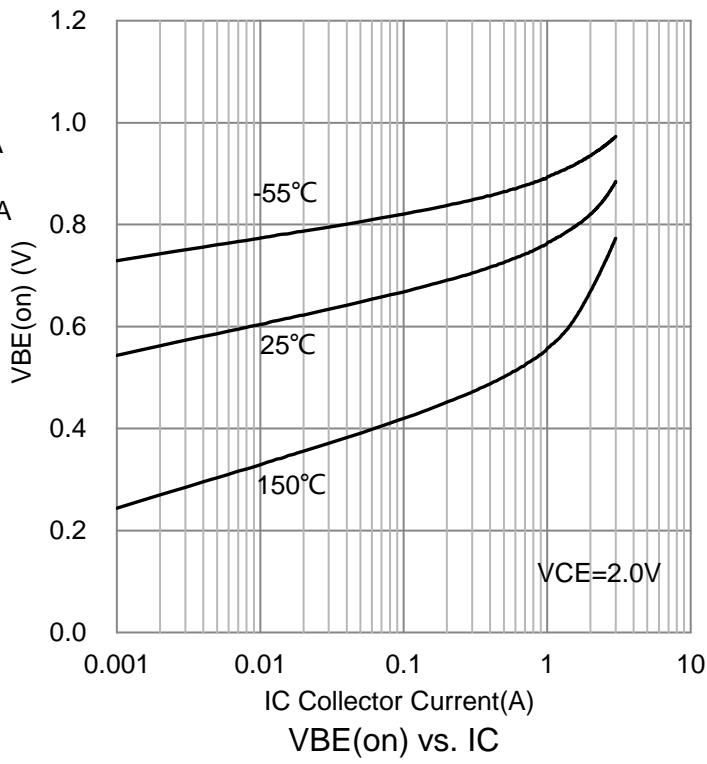
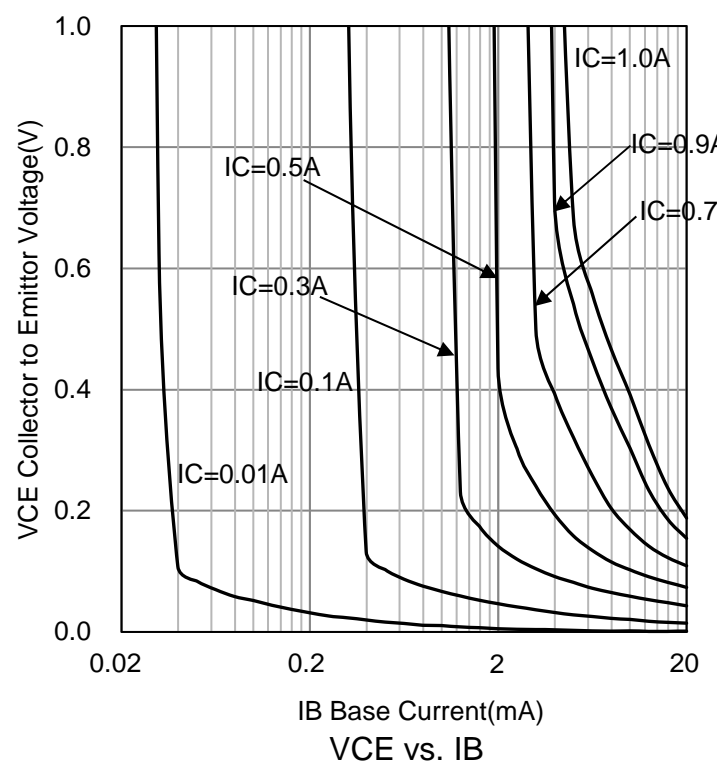
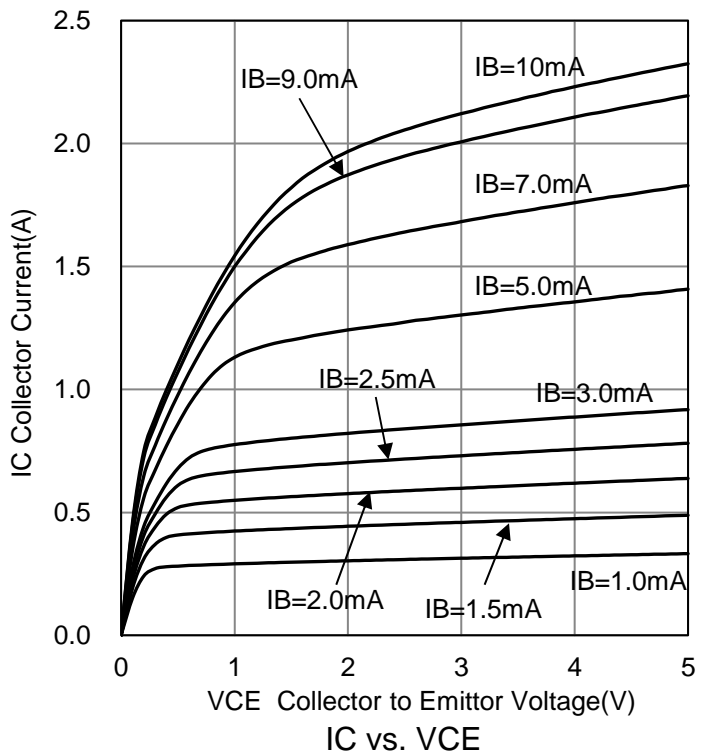
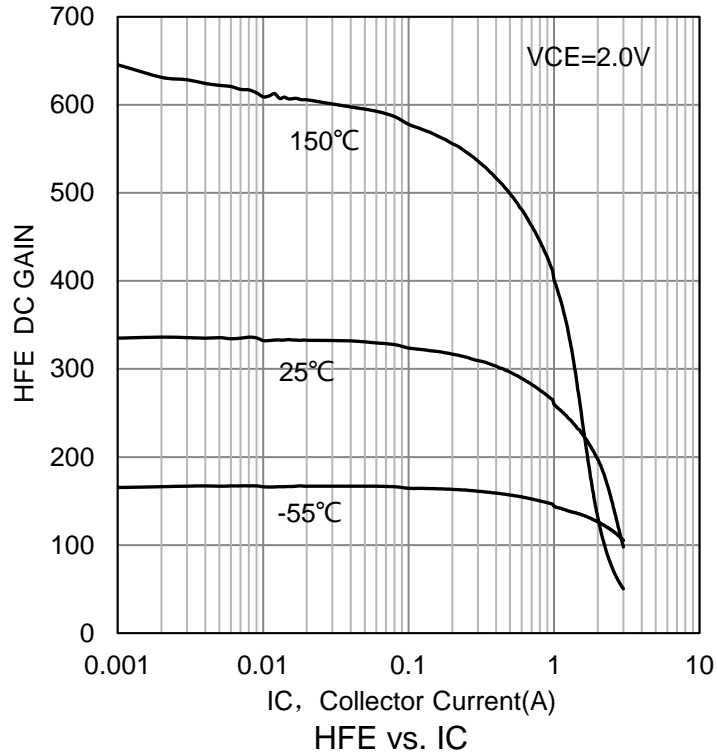
Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ TA = 25°C	PD	833	mW
Thermal Resistance, Junction–to–Ambient(Note 1)	RθJA	150	°C/W

1. FR-4 = 30.0mm×25.0mm×1.6mm.

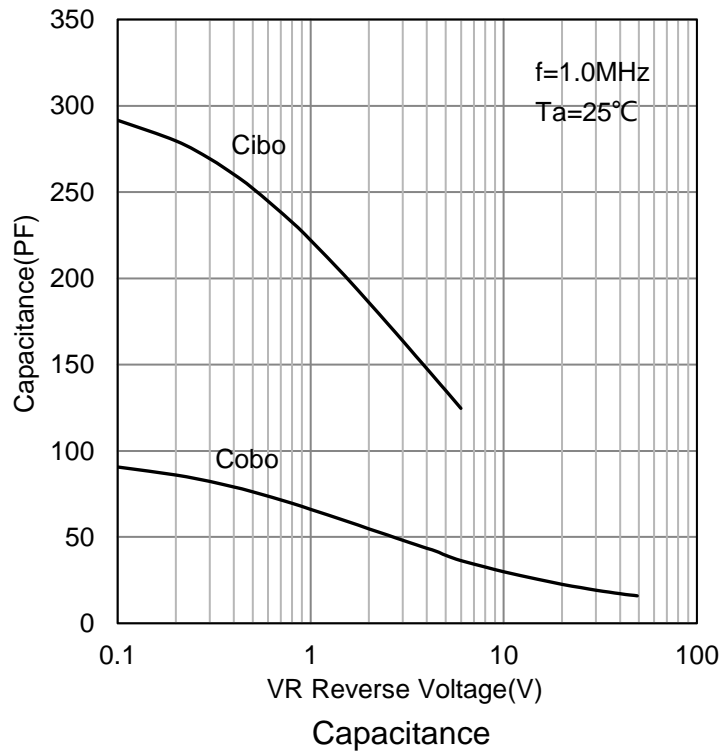
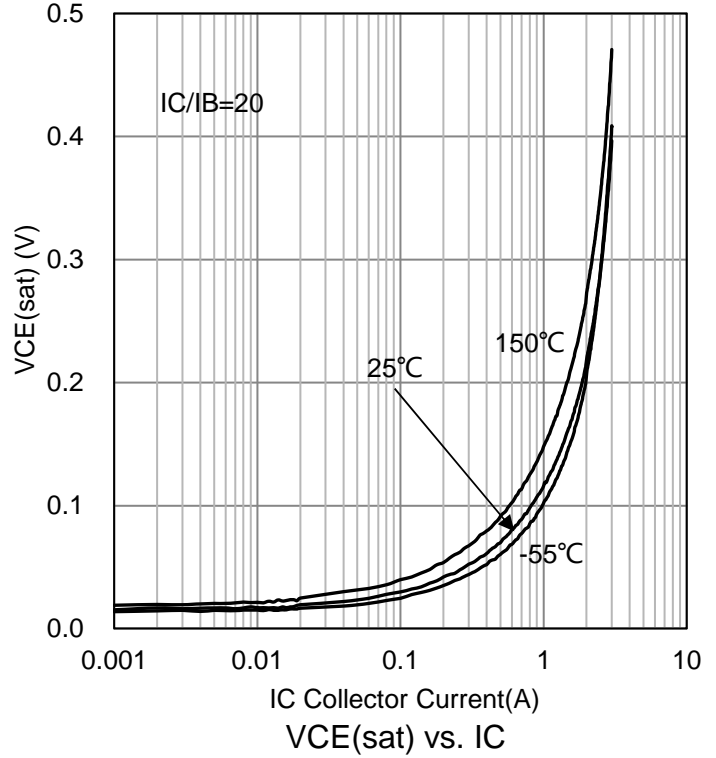
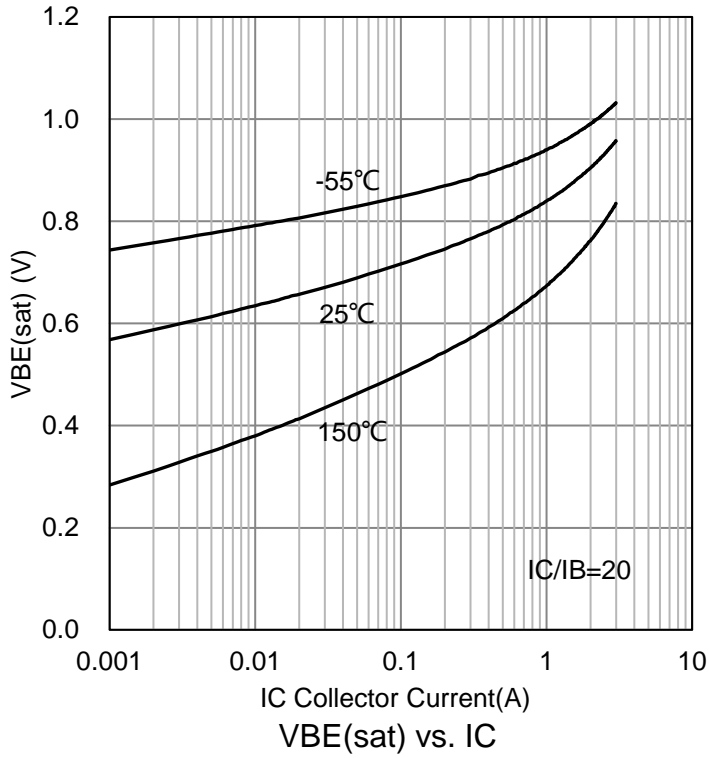
**5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)**

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = -1mA, IB = 0)	VBR(CEO)	-50	-	-	V
Collector–Base Breakdown Voltage (IC = -100 μA, IE = 0)	VBR(CBO)	-60	-	-	V
Emitter–Base Breakdown Voltage (IE = -100 μA, IC = 0)	VBR(EBO)	-6	-	-	V
Collector Cutoff Current (VCB = -40 V, IE = 0)	ICBO	-	-	-1	μA
Emitter Cut-off Current (VEB = -4V, IC = 0)	IEBO	-	-	-1	μA
Collector-Emitter cutoff Current (VCE = -50V, IB = 0)	ICEO	-	-	-10	μA
DC Current Gain (VCE = -2V, IC = -100mA) (VCE = -2V, IC = -3A)	HFE	200 35	- -	400 -	
Collector–Emitter Saturation Voltage (IC = -2A, IB = -100mA)	VCE(sat)	-	-0.35	-0.7	V
Base-Emitter saturation voltage (IC = -2A, IB = -100mA)	VBE(sat)	-	-0.94	-1.2	V
Transition Frequency (VCE = -10V, IC = -50mA)	fT	-	150	-	MHz
Collector Output Capacitance (VCB = -10V, f = 1MHz)	Cob	-	39	-	pF

6.ELECTRICAL CHARACTERISTICS CURVES

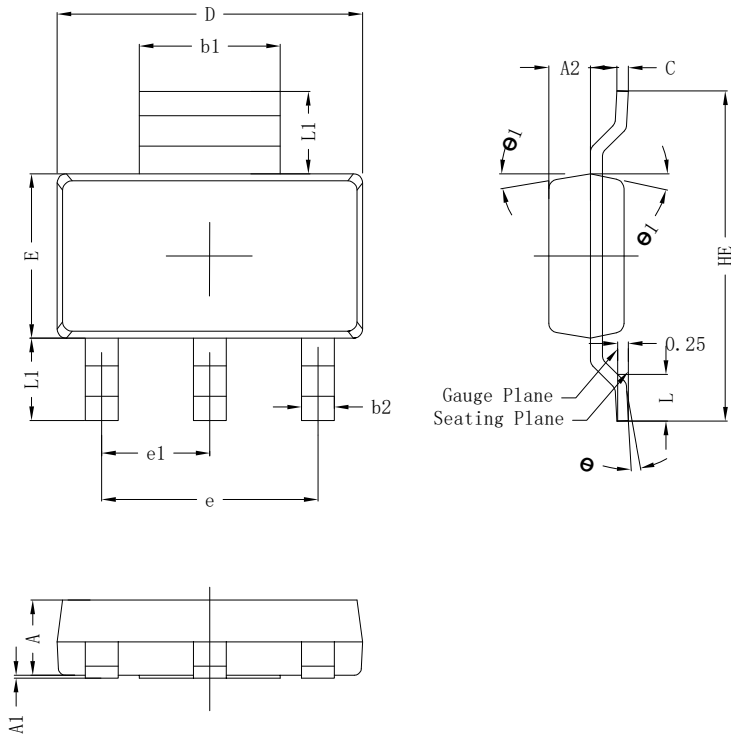


6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



### 7.OUTLINE AND DIMENSIONS

#### SOT223

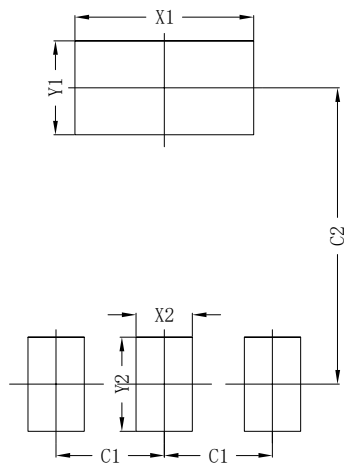


SOT223			
DIM	MIN	NOR	MAX
A	1.50	1.60	1.70
A1	0.00	0.05	0.10
A2	0.80	0.90	1.00
b1	2.90	3.02	3.10
b2	0.60	0.72	0.80
c	0.20	0.27	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	4.60BSC		
e1	2.30BSC		
HE	6.80	7.00	7.20
L	0.80	1.00	1.20
L1	1.75(REF)		
θ	0°~8°		
θ 1	8°	10°	12°
All Dimensions in mm			

#### GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um
4. Protrusion or Gate Burrs shall not exceed 0.10mm per side.

### 8.SOLDERING FOOTPRINT



SOT223	
DIM	(mm)
X1	3.80
Y1	2.00
X2	1.20
Y2	2.00
C1	2.30
C2	6.30

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